DISCRETE SEMICONDUCTORS

DATA SHEET

BT151U series C Thyristors

Product specification

August 2018



Thyristors

BT151U series C

GENERAL DESCRIPTION

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

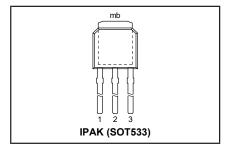
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | MAX. | UNIT |
|---|---|----------------------------|---------------------------------|---------------------------------|------------------|
| V _{DRM} , V _{RRM} I _{T(AV)} I _{T(RMS)} I _{TSM} | BT151U- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current | 500C 500 7.5 12 100 | 650C 650 7.5 12 100 | 800C 800 7.5 12 100 | V A A A |

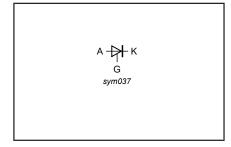
PINNING - SOT533, (I-PAK)

| PIN NUMBER | DESCRIPTION |
|---------------|-------------|
| 1 | cathode |
| 2 | anode |
| 3 | gate |
| tab | anode |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | | MAX. | | UNIT |
|--|---|--|---------------|-------------------------------|-------------------------------|---------------------|-------------|
| V _{DRM} , V _{RRM} | Repetitive peak off-state voltages | | - | -500C 500 ¹ | -650C 650 ¹ | -800C 800 | V |
| $\begin{matrix} I_{T(AV)} \\ I_{T(RMS)} \\ I_{TSM} \end{matrix}$ | Average on-state current RMS on-state current Non-repetitive peak on-state current | half sine wave; $T_{mb} \le 104 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge | - - | | 7.5 12 | | A A |
| 12. | | t = 10 ms t = 8.3 ms | - - | | 100 110 | | A A |
| l²t dl _⊤ /dt | I ² t for fusing Repetitive rate of rise of on-state current after triggering | t = 10 ms $I_{TM} = 20 \text{ A}; I_{G} = 50 \text{ mA};$ $dI_{G}/dt = 50 \text{ mA}/\mu\text{s}$ | - - | | 50 50 | | A²s A/μs |
| I _{GM} V _{RGM} P _{GM} | Peak gate current Peak reverse gate voltage Peak gate power | | - - - | | 2 5 5 | | A V W |
| $\begin{array}{c} P_{G(AV)} \\ T_{stg} \\ T_i \end{array}$ | Average gate power Storage temperature Junction temperature | over any 20 ms period | - -40 - | | 0.5 150 125 | | ů Ĉ W |

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------------|---|-------------|------|---------|----------|-------------------|
| $R_{th j-mb}$ $R_{th j-a}$ | Thermal resistance junction to mounting base Thermal resistance | in free air | - | - 70 | 1.3 - | K/W K/W K/W |
| th j-a | junction to ambient | in nee an | | 70 | | 10,00 |

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------------------|---------------------------|--|------|------|------|------|
| I _{GT} | Gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ | - | 2 | 15 | mA |
| l I | Latching current | $V_{\rm D}^{\rm S} = 12 \text{ V}; I_{\rm GT}^{\rm T} = 0.1 \text{ A}$ | - | 10 | 40 | mA |
| l I _H | Holding current | $V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$ | - | 7 | 20 | mA |
| ĺŸ⊤ | On-state voltage | $I_{T} = 23 \text{ A}$ | - | 1.44 | 1.75 | V |
| V _{GT} | Gate trigger voltage | $\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$ | - | 0.6 | 1.5 | V |
| | | $V_D = V_{DRM(max)}$; $I_T = 0.1 A$; $T_j = 125 °C$ | 0.25 | 0.4 | - | V |
| I _D , I _R | Off-state leakage current | $V_D = V_{DRM(max)}^{Station (max)}; V_R = V_{RRM(max)}; T_i = 125 °C$ | - | 0.1 | 0.5 | mΑ |

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------|--|---|-----------|-------------|------|--------------|
| dV _D /dt | Critical rate of rise of off-state voltage | $\begin{array}{c} V_{\text{DM}} = 67\% \ V_{\text{DRM(max)}}; T_j = 125 \ ^{\circ}\text{C}; \\ \text{exponential waveform} \\ \text{Gate open circuit} \\ R_{\text{GK}} = 100 \ \Omega \end{array}$ | 50 200 | 130 1000 | - | V/μs V/μs |
| t _{gt} | Gate controlled turn-on time | $I_{TM} = 40 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; \\ dI_G/dt = 5 \text{ A}/\mu\text{s}$ | - | 2 | - | μς |
| t _q | Circuit commutated turn-off time | $V_D = 67\% \ V_{DRM(max)}; T_j = 125 \ ^{\circ}C; I_{TM} = 20 \ A; V_R = 25 \ V; dI_{TM}/dt = 30 \ A/\mu s; dV_D/dt = 50 \ V/\mu s; R_{GK} = 100 \ \Omega$ | - | 70 | - | μs |

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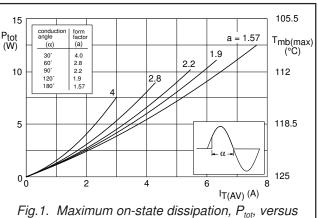


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$.

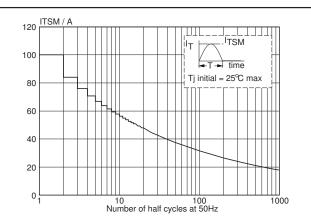


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

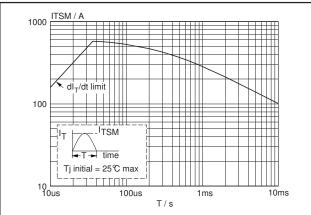


Fig.2. Maximum permissible non-repetitive peak on-state current l_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

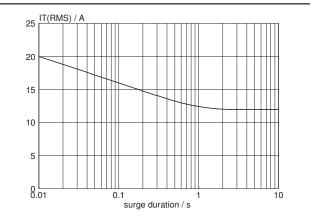


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 100$ °C.

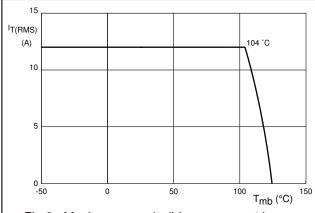
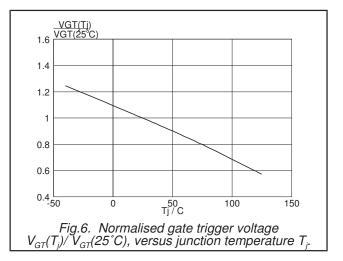
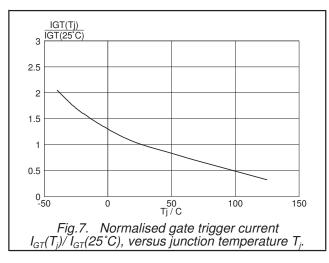
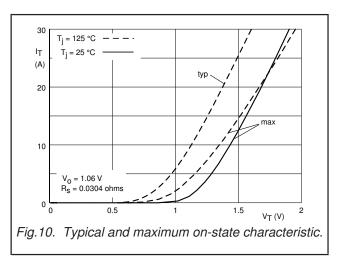


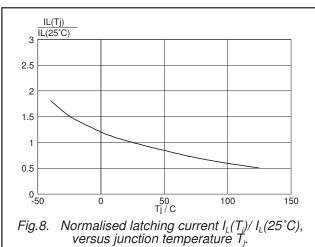
Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

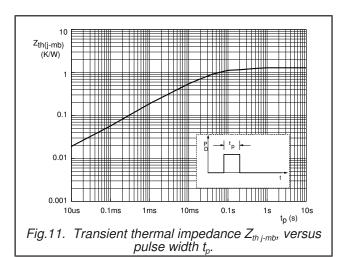


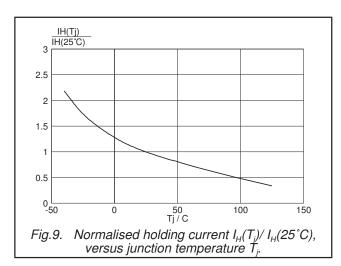
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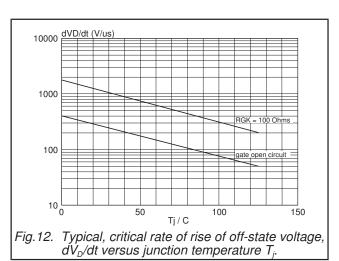












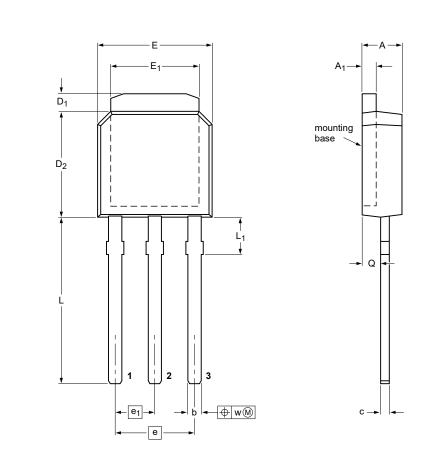
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MECHANICAL DATA



SOT533



DIMENSIONS (mm are the original dimensions)

| ι | JNIT | Α | A ₁ | b | С | D ₁ | D ₂ | Е | E ₁ | е | e ₁ | L | L ₁ ⁽²⁾ max | ď | w |
|---|------|---|----------------|---|---|----------------|----------------|---|----------------|---|-----------------------------|---|--------------------------------------|------------|-----|
| | mm | | | | | | | | | | 2.285 BSC ⁽¹⁾ | | 2.7 | 1.1 1.0 | 0.3 |

Notes

- 1. Basic spacing between centers.
- 2. Terminal dimensions are uncontrolled within zone L_1 .

| OUTLINI | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|--------|-------|------------|----------------------------------|
| VERSIO | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT533 | | TO-251 | | | -05-02-11 06-02-14 |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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